



ELBE^{*} – Center for High-Power Radiation Sources



Defects and Hydrogen in Nb films

*Electron Linear accelerator with high Brilliance and low Emittance

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Energy



Matter



Health

HZDR outposts Freiberg Görlitz (CASUS) Grenoble (ESRF) Hamburg (European XFEL) Leipzig Rostock



Key Technologies



Earth & Env.



Space & Transport

Resource technologies Complex systems ROBL beamline HiBEF Radioisotopes High energy density physics

Hermann von Helmholtz

1821 - 1894

HELMHOLTZ

HZDR - large scale research infrastructures



ELBE. SC electron CW-LINAC



PW-class lasers Laser particle acceleration





IBC. Ion beam center



Tech transfer and industry services



HLD.

> 90 T magnets

Proton tumor therapy and

OncoRay

250 MeV protons





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User facilities and science cases



γ - rays 0 – 20 MeV

Superradiant THz

0.1 – 2.5 THz, 300 kV/cm 120 μm – 3 mm, 10-250 kHz

IR-FELs

5 – 250 µm, 2 µJ 1.2 – 60 THz, 13 MHz

Neutrons

0.1 – 10 MeV 10⁴ n/(s cm²), 100 kHz

Positrons 0.5 – 20 keV,

 $5.10^{6} \text{ e}^{+/s}$

Direct electrons 10 – 40 MeV • Nuclear physics – e-m strength in heavy nuclei

- Nuclear astrophysics synthesis of elements
- In-sample positron generation
- Ultra-fast dynamics at fs time scales
- Non-linear dynamics, spin-wave coupling
- Materials for high-bandwidth data transmission
- Near-field microscopy
- Semiconductor spectroscopy, quantum dots
- Small bandwidth
- Materials for fusion reactors
- Nuclear transmutation
- Neutron time-of-flight
- Solid state physics spectroscopy of defects
- Thin film semiconductors
- Porosimetry
- Rad. biology high local dose rates
- Technological developments
- Isotope production

ELBE Center for High-Power radiation Sources



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Superconducting Accelerator

250 pC (1 nC WIP)

SC resonant cavities developed by TESLA Technology Collaboration. Employed in CEBAF, FLASH, **ELBE**, EU-XFEL, LCLS-II, Lighthouse,...



Mainly serves cTHz and photo-neutron source at 10 – 250 kHz



The e⁺ probes...

- local electron density and electron momentum
- defect sizes and types by annihilation lifetime

- defect concentrations by component's intensity
- large volumes due to large diffusion lengths



MePS – The Mono-energetic Positron Source @ ELBE



Positron Annihilation: basics

- Decomposing positron annihilation lifetime distribution
 - Lifetime correlates with size of cluster vacancies





$$f(t) = \sum_{j=1}^{k_0} (a_j * R)(t) + B$$
$$a_j(t) = \begin{cases} A_j \exp(-t/\tau_j), & t > 0\\ 0, & t < 0 \end{cases}$$





J. Čižek et al., Phys Rev B79, 054108 (2009) J. Čižek et al., Phys. Rev. B69, 224106 (2004)

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Vacancy kinetics during in-situ low-T baking

v+nH complex dynamics in surface near region





- T ≥ 390 K: shows most significant changes (already after short times)
 - v+nH concentration (I₂) decreases
 - hydrogen release from the complexes (τ₂ increases)
 - defect type and surface states start to change (τ₃ increases)

M. Wenskat, et al. "Vacancy-Hydrogen interaction in **niobium** during Low-temperature Baking." *Scientific reports 10.1 (2020) 8300*

M. Wenskat, et al. "Vacancy dynamics in **niobium** and its native oxides and their potential implications for quantum computing and superconducting accelerators" *Phys. Rev. B* 106 (2022) 094516

L. Chiari, et al. "Formation and time dynamics of hydrogen-induced vacancies in **nickel**" *Acta Materialia* 219 (2021) 117264

Positron Science Cases

 Pulsed beams: annihilation lifetime spectroscopy for thin films, bulk materials, fluids, gases and (coincidence) Doppler broadening spectroscopy



porous glasses, membranes, metal-organic frameworks



low-k dielectrics for CMOS devices





magnetic phase transitions through ion irradiation



Hydrogen-induced vacancies in Ni



semiconductors

for optoelectronics

Niobium-hydrides & superconductivity



micro-solid oxide fuel cells



Positrons in matter – fundamentals to materials research

- porosimetry on the nm-scale
 - Iow-k SiO₂ for CMOS devices (DFG)
 - gas-separation membranes
- single⁺-vacancy defect analysis
 - superconductors (H in Nb for SRF, YBCO)
 - FeCr, ODS, HEA for fission/fusion
 - Semiconductors (ZnO, CIGS, Ge, Ga₂O₃,)
 - defect-induced magnetism (FeRh)
 - magneto-ionics (O₂ or N₂-mediated)
- chemical environment of defects
 - decoration, alloying, segregation
- positronium chemistry (medicine)







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Accelerator-driven positron sources



Accelerator-driven positron sources



Positron User Facilities



Mono-energetic Positron Source

- 35 MeV, 200 µA, 1.625 MHz electron beam drives
- 0.5 16 keV e⁺ beam for PALS 300 K – 550 K sample temperature typically 250 kcps event rate (120 kcps at 511 keV)
- 10 Mevts PALS spectrum in 80 s, fully digital data taking and online processing A.Wagner, et al., AIP Conf. Proc. 1970, 040003 (2018)

SPONSOR

 ²²Na-based (2 GBq) e⁺ beam 30 eV – 30 keV for CDBS coupled to

AIDA

- 35K -1300 K
- MBE, ion irradiation
- sheet resistance



W. Anwand, et al., Def & Diff. Forum 331 (2012) 25

Gamma-ray induced Positron

- 16 MeV, 700 µA electron beam generates
 bremsstrahlung
- e⁺ formed inside sample
- Suitable for radioactive samples, gases, fluids

M. Butterling, et al., Nucl. Instr. Meth. B 269, 2623 (2011)

Hydrogen and defects in Niobium – SC cavities



TESLA-type SRF cavities are used at CEBAF@JLAB, FLASH & XFEL (Hamburg), ELBE@HZDR Dresden, MESA (Mainz) Cu: $R_s = 10 \text{ m}\Omega$, $Q_0 = 10^3 \dots 10^4$, max gradient 1 MV/m Nb: $R_s = \text{few n}\Omega$, $Q_0 = 10^{10} \dots 10^{11}$, max gradient 50 MV/m, operated at 2...4 K

A. Arnold et al., Proc LINAC2014, Geneva, Switzerland

Thermal cavity treatment

- Q disease
- increase of the surface losses at cryogenic temperatures
- sets in even at low values of the applied accelerating field











Curing Q disease

- rapid cool down inhibits the hydride formation
 - can cause damages due to thermal stress
- typical procedure^{1,2} to increase Q and keep the H concentration below 10 ppm
 - chemical polishing (remove up to 100 µm), but incorporates H
 - baking at 1050 K for 3 h in vacuum (< 10⁻⁵ mbar) to remove H
 - several hundreds ppm of H remain in the lattice in the near-surface layer
 - chemical polishing (remove up to 100 µm), again incorporates H
 - mild bake: at 390 K for 48 h (< 10⁻⁶ mbar) to avoid high-field Q slope (accidentally found!)
 - low-T bake³: only 350 K for first 2 h
 - \rightarrow Q losses reduced by factor 2
 - \rightarrow increased achievable accelerating field by >10%







P. Kneisel et al., AIP Con Proc 927, 84 (2007) JLAB
 G. Ciovati et al., Phys Rev Acc & Beams 13.2, 022002 (2010), JLAB
 A. Grassellino et al., arXiv 1806.09824 (2018)

Vacancy kinetics

In-situ baking at MePS





- Mono-energetic Positron Source MePS at HZDR:
- depth-resolved PALS up to 10 keV (in 2019)
- high intensity: 10⁶ counts in 2 minutes
- well-suited for study of dynamic effects

In-situ measurements

- in-situ baking at different temperatures for 4 hours and measuring at different energies all the time
- depth profile at 340 K after each annealing step

Vacancy dynamics

V+nH show complex dynamics near surface



40°C damp sunken pale even structure well risen golden brown uneven structure very uneven rise partly burnt using a fan oven

Effect of oven temperature on baking*

Collaboration: Hamburg U, DESY, HZ Berlin, U Wuppertal, U Siegen, U Kaiserslautern, U Bremen, CU Prague, CTU Prague



- T = 390 K: shows most significant changes (already after short times)
- T > 390 K: hydrogen released from complexes (τ₂ increases)
 v+nH concentration (I₂) decreases

Wenskat, M. et al. *Phys. Rev. B* 106(2022), 094516 Wenskat, M. et al. *Scientific Reports* 10(2020), 8300

Secondary beams: THz radiation – from electronics to photonics

1 THz $m \triangleq$ 300 μ m $m \triangleq$ 33 cm⁻¹ $m \triangleq$ 4.1 meV



in various units:

Frequency:	0.3 – 30 THz
Wavenumber:	10 – 1000 cm ⁻¹
Energy:	~1 – 100 meV
Wavelength:	1 mm – 10 µm

In some ranges no good laboratory (table-top) sources are available: THz, UV, X-ray

Secondary beams: Free-Electron Lasers

FEL – 1971 (Stanford), 2005 UV & 2017 X-ray (FLASH, DESY Hamburg)



Undulator parameter $\mathbf{K} = \theta \cdot \gamma = eBd/2\pi mc \sim 1$

(θ is the maximum electron deflection angle, 1/ γ is also the width of the emitted radiation cone) $\lambda_{\rm L} = \frac{\lambda_{\rm u}}{2\gamma^2} \left(1 + \frac{K^2}{2} \right)$

wavelength of undulator radiation

THz pulses as pump for nonlinear dynamics



- Coherent **selective excitation** of relevant modes, avoiding parasitic electronic excitation
- How and on what timescales do degrees of freedom interact?
- Strong modifications of macroscopic properties possible → phase transitions, metastable states, tailored functionality, quasiparticle excitations

THz science cases

Control of Materials with THz light



- Electronic or structural phase transitions
- THz nonlinear optics
- Superconductivity
- Spin dynamics
- Exotic quantum properties

→ Materials and processes for information and energy technology

Selective Chemistry

- Trigger for reactions
- Steering reaction pathway
- Temperature jumps

→ Catalytic materials and processes, fundamentals of water chemistry

Biology in highest electric fields

- Hydration shell dynamics

➤ intracellular

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- Potential-driven processes in aqueous solutions

→ Elementary cellular mechanisms

Vacancy kinetics during in-situ low-T baking

In-situ Positron Annihilation Lifetime Spectroscopy at pELBE



In-situ measurements

- in-situ baking at different temperatures for 4 hours and measuring at different energies all the time
- depth profile at 340 K after each annealing step

- focus on the vacancy dynamics: measurement during temperature treatment
- study two different material depths: 20 nm and 80 nm (RF layer ~ 100 nm)